

P-Ch MOSFET

#### **General Description**

The WST2035 is the highest performance trench P-Ch MOSFET with extreme high cell density , which provide excellent RDSON and gate charge for most of the synchronous buck converter applications .

The WST2035 meet the RoHS and Green Product requirement , with full function reliability approved.

#### Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Green Device Available

#### **Product Summery**

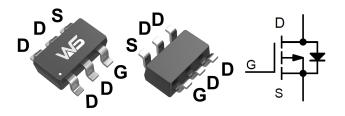
BVDSS	RDSON	ID
-20V	37mΩ	-4A

#### Applications

- Portable Equipment and Battery Powered Systems.
- Power Management in Notebook

Computer

#### SOT- 23-6L Pin Configuration



#### **Absolute Maximum Ratings**

Symbol	Parameter	Rating	Units
V <sub>DS</sub>	Drain-Source Voltage	-20	V
V <sub>GS</sub>	Gate-Source Voltage	±8	V
I <sub>D</sub> @T <sub>A</sub> =25℃	Continuous Drain Current, V <sub>GS</sub> @ -4.5V <sup>1</sup>	-4	А
I <sub>D</sub> @T <sub>A</sub> =70℃	Continuous Drain Current, V <sub>GS</sub> @ -4.5V <sup>1</sup>	-3.2	A
I <sub>DM</sub>	Pulsed Drain Current <sup>2</sup>	-30	Α
P <sub>D</sub> @T <sub>A</sub> =25℃	Total Power Dissipation <sup>3</sup>	0.35	W
T <sub>STG</sub>	Storage Temperature Range	-55 to 150	°C
TJ	Operating Junction Temperature Range	-55 to 150	°C

#### **Thermal Data**

Symbol	Parameter	Тур.	Max.	Unit
R <sub>θJA</sub>	Thermal Resistance Junction-Ambient <sup>1</sup>		357	℃/W
R <sub>θJC</sub>	Thermal Resistance Junction-Case <sup>1</sup>		85	°C/W



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#### Electrical Characteristics (T<sub>J</sub>=25<sup>-1</sup>C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit	
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS}$ =0V , I <sub>D</sub> =-250uA	-20			V	
$\triangle BV_{DSS} / \triangle T_J$	BV <sub>DSS</sub> Temperature Coefficient	Reference to 25 $^\circ\!\!{\rm C}$ , I_D=-1mA		-0.016		V/℃	
Б	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =-4.5V , I <sub>D</sub> =-4.0A		37	50		
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =-2.5V , I <sub>D</sub> =-4.0A		45	60	mΩ	
V <sub>GS(th)</sub>	Gate Threshold Voltage		-0.3	-0.56	-1.0	V	
$ riangle V_{GS(th)}$	V <sub>GS(th)</sub> Temperature Coefficient	$-V_{GS} = V_{DS}$ , $I_D = -2500A$		3.97		mV/℃	
	Drain Source Lookage Current	$V_{\text{DS}}\text{=-20V}$ , $V_{\text{GS}}\text{=}0\text{V}$ , $T_{\text{J}}\text{=}25^\circ\!\mathrm{C}$			-1		
I <sub>DSS</sub>	Drain-Source Leakage Current $V_{DS}=20V$ , $V_{GS}=0V$ , $T_J=125$ °C				-30	uA	
I <sub>GSS</sub>	Gate-Source Leakage Current	$V_{GS}=\pm10V$ , $V_{DS}=0V$			±100	nA	
gfs	Forward Transconductance	V <sub>DS</sub> =-5V , I <sub>D</sub> =-3A	8	16		S	
Qg	Total Gate Charge (-4.5V)			17.2			
Q <sub>gs</sub>	Gate-Source Charge	$V_{\text{DS}}\text{=-}16\text{V}$ , $V_{\text{GS}}\text{=-}4.5\text{V}$ , $I_{\text{D}}\text{=-}4.0\text{A}$		1.3		nC	
Q <sub>gd</sub>	Gate-Drain Charge			4.5			
T <sub>d(on)</sub>	Turn-On Delay Time			9.5			
Tr	Rise Time	$V_{DD}$ =-10V , $V_{GEN}$ =-4.5V ,		17		ns	
T <sub>d(off)</sub>	Turn-Off Delay Time	R <sub>G</sub> =6Ω, I <sub>D</sub> =-4A		94		115	
T <sub>f</sub>	Fall Time			35			
C <sub>iss</sub>	Input Capacitance			1450			
Coss	Output Capacitance	V <sub>DS</sub> =-10V , V <sub>GS</sub> =0V , f=1MHz		205		рF	
C <sub>rss</sub>	Reverse Transfer Capacitance			160			

#### **Diode Characteristics**

Symbol	Parameter	Parameter Conditions		Тур.	Max.	Unit
ls	Continuous Source Current <sup>1,4</sup>				-1.0	A
I <sub>SM</sub>	Pulsed Source Current <sup>2,4</sup>	V <sub>G</sub> =V <sub>D</sub> =0V , Force Current			-4.0	A
V <sub>SD</sub>	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V , I <sub>S</sub> =-1A , T <sub>J</sub> =25℃			-1.2	V
t <sub>rr</sub>	Reverse Recovery Time			9.5		nS
Qrr	Reverse Recovery Charge	IF=-4.0A,dI/dt=100A/µs , Tյ=25℃		94		nC

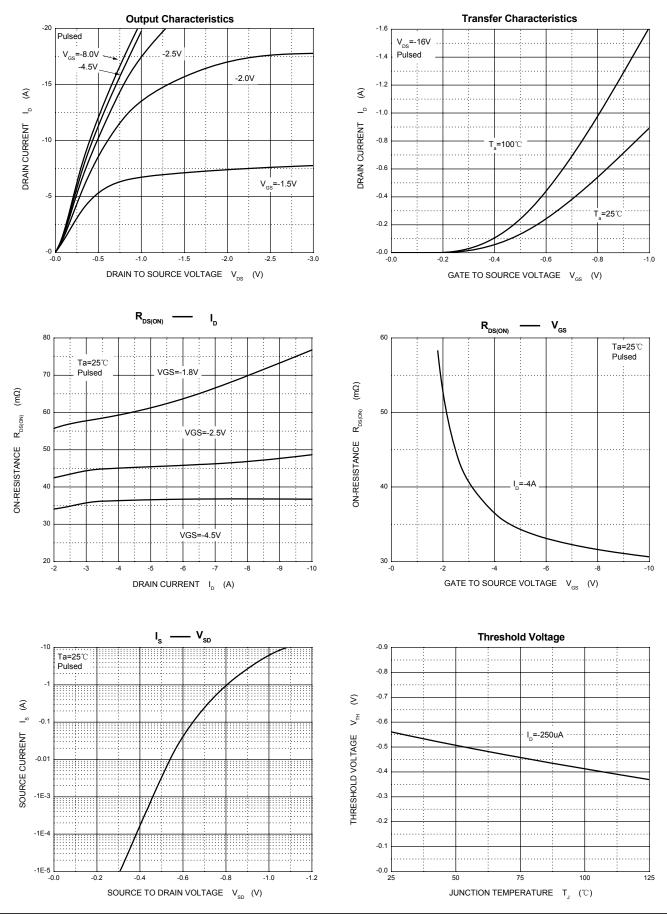
#### Notes:

- 1. Repetit e rating, pulse width limited by junction temperature.
- 2. Puls Test : Pulse width  $\leq$  300µs, duty cycle  $\leq$  2%.
- 3. These parameters have no way to verify.



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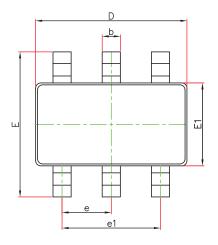
# **Typical Characteristics**

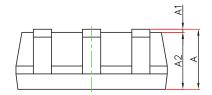


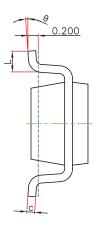


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## SOT-23-6L Package Outline Dimensions

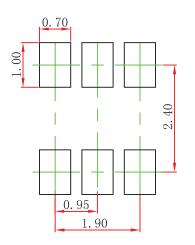






Symbol	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
A	1.050	1.250	0.041	0.049	
A1	0.000	0.100	0.000	0.004	
A2	1.050	1.150	0.041	0.045	
b	0.300	0.500	0.012	0.020	
С	0.100	0.200	0.004	0.008	
D	2.820	3.020	0.111	0.119	
E1	1.500	1.700	0.059	0.067	
E	2.650	2.950	0.104	0.116	
е	0.950(BSC)		0.037	(BSC)	
e1	1.800	2.000	0.071	0.079	
L	0.300	0.600	0.012	0.024	
θ	0°	8°	0°	8°	

### SOT-23-6L Suggested Pad Layout



Note:

1.Controlling dimension: in millimeters.

- 2.General tolerance:± 0.05mm.3.The pad layout is for reference purposes only.



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